

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Substitute for form 1449/PTO)				ATTY. DOCKET NO. <b>061282-0234</b>		SERIAL NO. <b>10/574,863</b>	
				APPLICANT <b>Yuichiro SASAKI, et al.</b>			
				FILING DATE <b>April 06, 2006</b>		GROUP <b>2823</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US 5,915,196	06-22-1999	MINEJI			
		US 6,153,524	11-28-2000	HENLEY et al.			
		US 6,159,810	12-12-2000	YANG			
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<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code <sup>3</sup> -Number 4-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No	
		WO 03/014979 A	02-20-2003	APPLIED MATERIALS, INC.		X	
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<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		International Search Report issued in International Patent Application No. PCT/JP2005/009949 dated July 5, 2005					
		International Search Report issued in International Patent Application No. PCT/JP2004015308 mailed January 18, 2005					
		Japanese Notification of Reasons for Refusal, w/ English translation thereof, issued in Japanese Patent Application No. JP 2005-502685 dated May 19, 2009					
		European Search Report issued in European Patent Application No. EP 04710478 dated May 12, 2009					
EXAMINER /George Fourson/				DATE CONSIDERED 03/11/2010			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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SHEET 2 OF 2

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		<b>US 2002/0006689 A1</b>	<b>01-17-2002</b>	<b>MIYASAKA, MITSUTOSHI</b>			
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number 4-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes      No
		<b>JP 7-142421</b>	<b>06-02-1995</b>	<b>NIPPON ELECTRIC CO</b>			<b>JAPAN (w/English Abstract)</b>
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<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		<b>TSUTSUI, K., et al., "Contribution and Control of Neutral Gas Absorption Effects in the Plasma Doping of Boron into Si", 2004, pages 46-49, IEEE.</b>					
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		<b>R. SIEGELE, et al., "Helium Bubbles in silicon: Structure and optical properties," Appl. Phys. Lett. 66 (11), 13 March 1995, pp. 1319-1321</b>					
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EXAMINER /George Fourson/				DATE CONSIDERED 03/11/2010			

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